



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	70mΩ@-4.5V	-2.3A
	110mΩ@-2.5V	

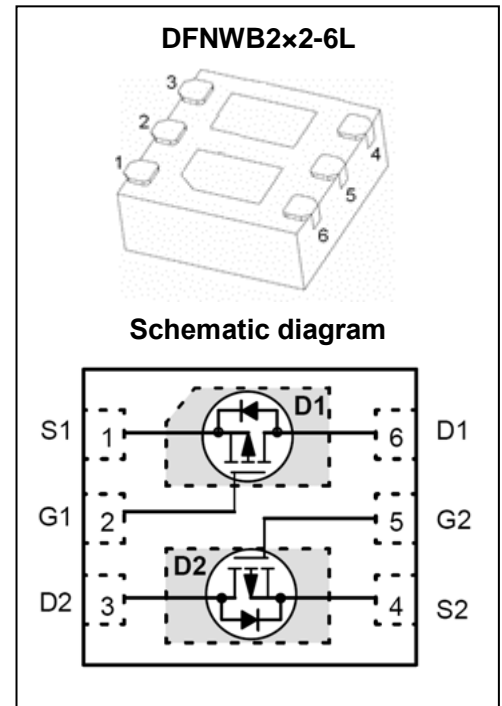
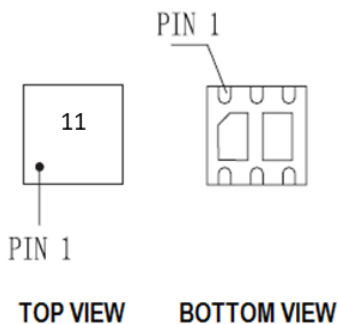
Feature

- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$ and Low Gate Charge

Application

- Optimized for Battery and Load Management Applications in Portable Equipment
- Li-Ion Battery Charging and Protection Circuits
- High Power Management in Portable , Battery Powered Products
- High Side Load Switch

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-2.3	A
Pulsed Drain Current	I_{DM}	-10	A
Power Dissipation	P_D	0.7	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	178	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

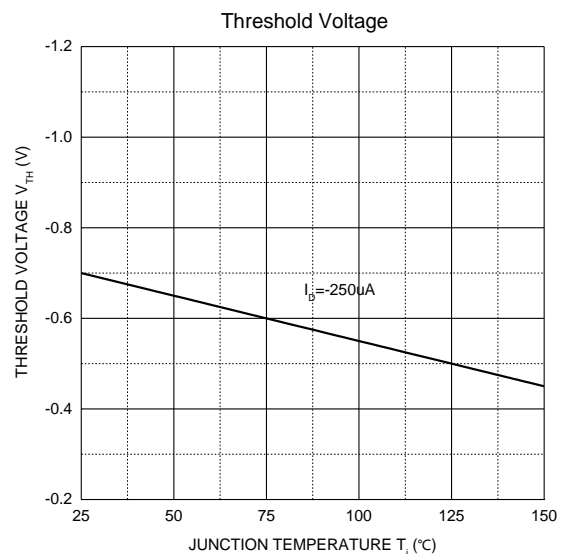
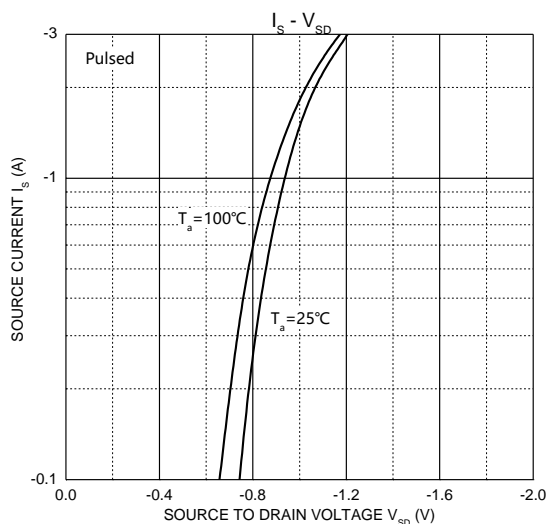
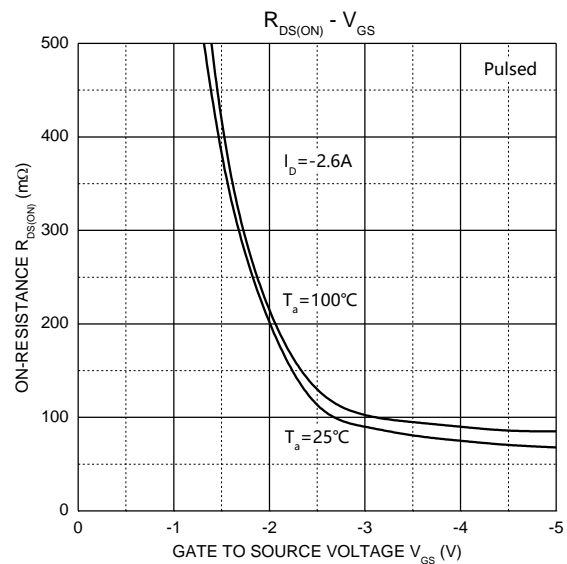
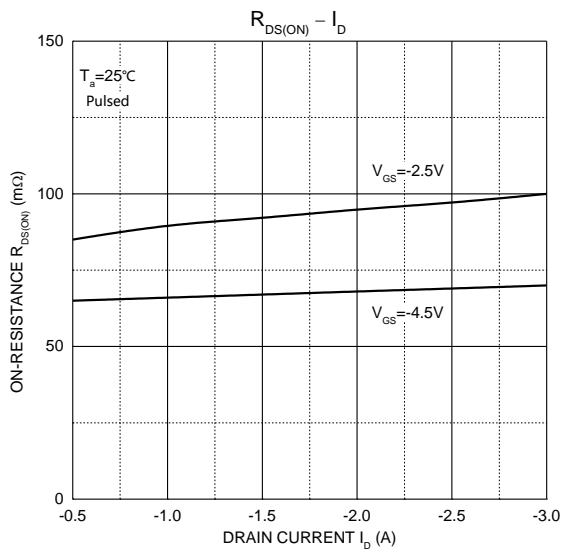
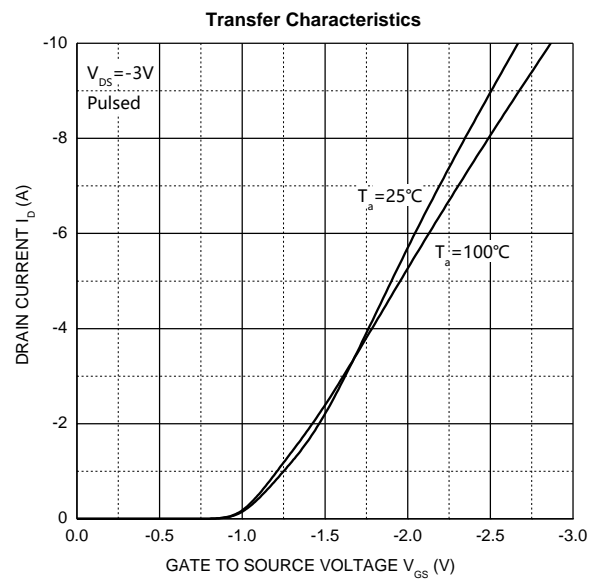
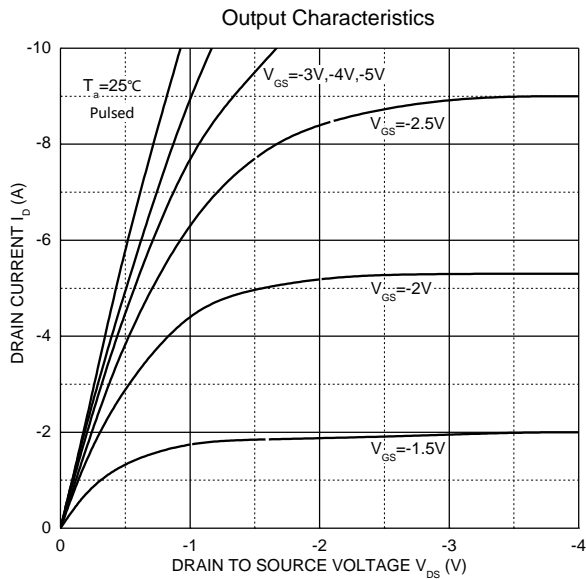
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -18V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±8V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.7	-1	V
Drain-source on-resistance ^a	R _{DS(on)}	V _{GS} = -4.5V, I _D = -2.8A		70	90	mΩ
		V _{GS} = -2.5V, I _D = -2A		100	130	
Dynamic characteristics^b						
Input Capacitance	C _{iss}	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz		363		pF
Output Capacitance	C _{oss}			70		
Reverse Transfer Capacitance	C _{rss}			60		
Gate resistance	R _g	f = 1MHz			50	Ω
Total Gate Charge	Q _g	V _{DS} = -10V, V _{GS} = -2.5V, I _D = -3A		3.2		nC
Gate-Source Charge	Q _{gs}			0.6		
Gate-Drain Charge	Q _{gd}			1.2		
Turn-on delay time	t _{d(on)}	V _{DD} = -10V, V _{GEN} = -4.5V, I _D = -1A R _L = 10Ω, R _{GEN} = 1Ω		9		ns
Turn-on rise time	t _r			33		
Turn-off delay time	t _{d(off)}			29		
Turn-off fall time	t _f			9		
Source-Drain Diode characteristics						
Diode forward current	I _S	T _C = 25°C			-2.3	A
Diode pulsed forward current ^a	I _{SM}				-10	A
Diode Forward voltage	V _{DS}	V _{GS} = 0V, I _S = -1.3A			-1.2	V

Notes :

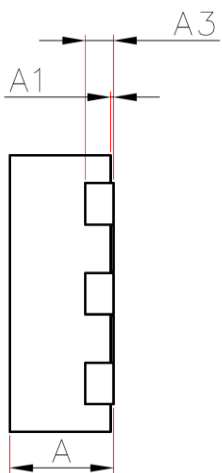
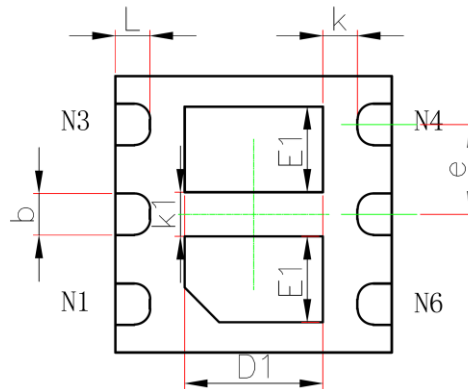
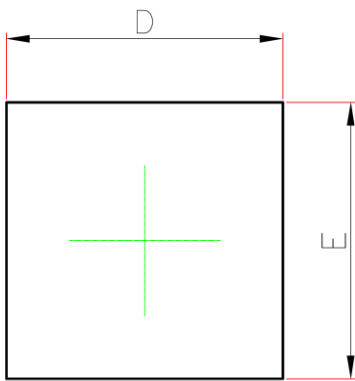
a. Pulse Test : Pulse Width < 300μs, Duty Cycle ≤2%.

b. Guaranteed by design, not subject to production testing

Typical Electrical and Thermal Characteristics



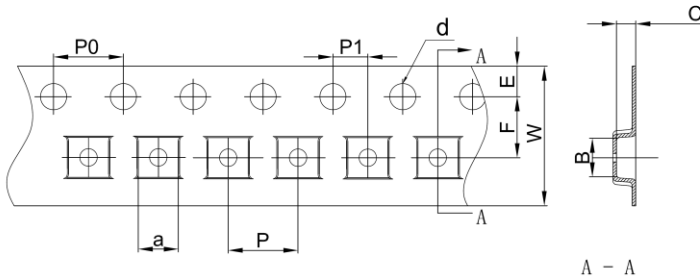
DFNWB2x2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN.	MAX.	MIN.	MAX.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.900	1.100	0.035	0.043
E1	0.520	0.720	0.020	0.028
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
k	0.200MIN.		0.008MIN.	
k1	0.320REF.		0.013REF.	
L	0.200	0.300	0.008	0.012

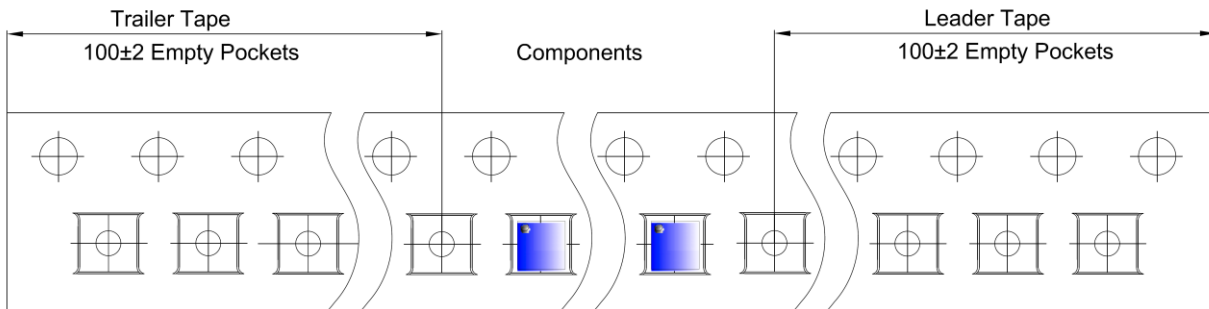
DFNWB2×2-6L Tape and Reel

DFNWB2×2-6L Embossed Carrier Tape

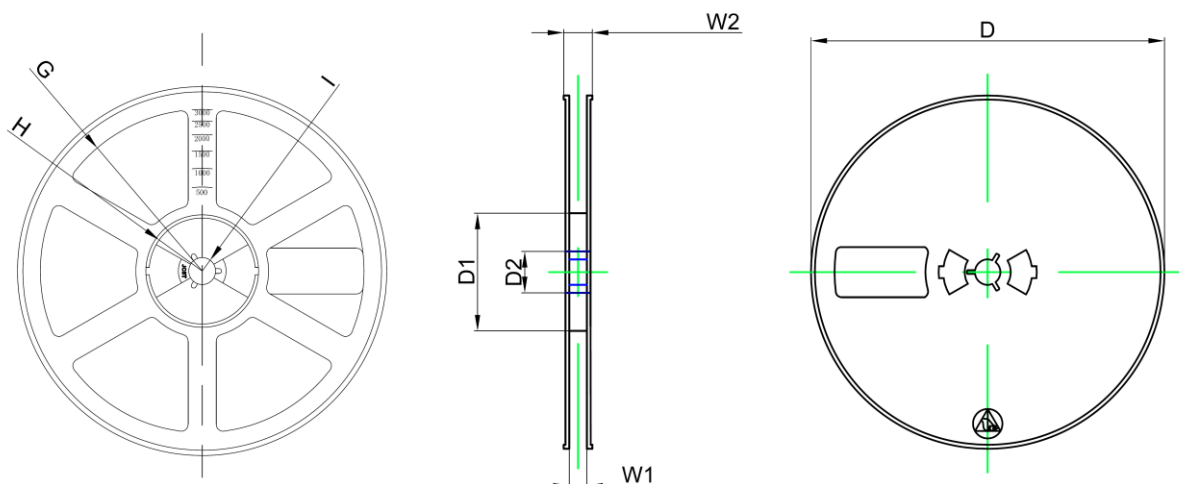


Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)